Discrete POWER & Signal **Technologies**

PN5138

FAIRCHILD SEMICONDUCTOR TM

PN5138



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	30	V	
V_{EBO}	nitter-Base Voltage 5.0		V	
I _C	Collector Current - Continuous 500		mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

 $R_{\theta JA}$

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thormal Charactoristics

TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		PN5138	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	200	°C/W

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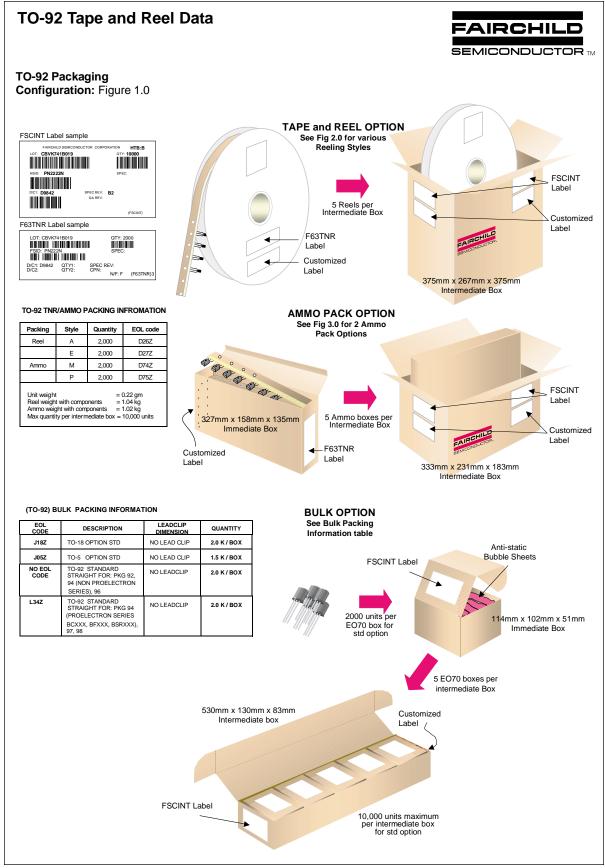
PNP General Purpose Amplifier

		PNP Gene	eral Pur	pose A	(continued
Electrical Characteristics TA = 25°C unless otherwise noted					
ymbol	Parameter	Test Conditions	Min	Max	Units
FF CHAI	RACTERISTICS				
BR)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30		V
BR)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	30		V
BR)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu {\rm A}, I_{\rm C} = 0$	5.0		V
0	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$ $V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0, \text{ T}_{A} = 65 ^{\circ}\text{C}$		50 3.0	nA μA
N CHAR	ACTERISTICS*				
E	DC Current Gain	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 0.1 \mu\text{A}$	50	800	
		$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	50 50		
E(sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA	50	0.3	V
E(sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.0	V
	Base-Emitter On Voltage	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$		1.0	V

SMALL SIGNAL CHARACTERISTICS

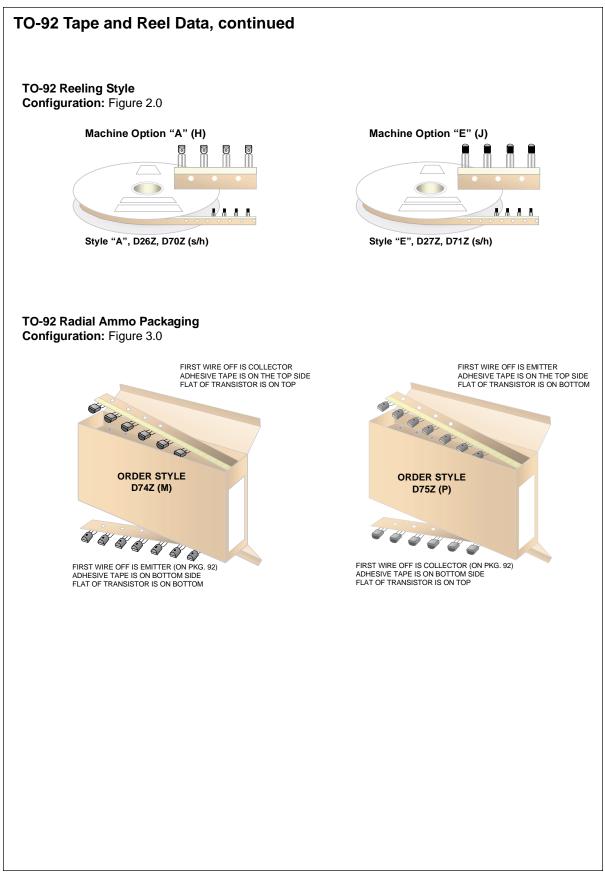
Cob	Output Capacitance	$V_{CB} = 5.0 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		7.0	pF
C _{ib}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		30	pF
h _{fe}	Small-Signal Current Gain	$ I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, $ f = 1.0 kHz I_{C} = 0.5 mA, V_{CE} = 5.0 \text{ V}, f = 20 \text{ MHz}	40 1.5	1000	

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

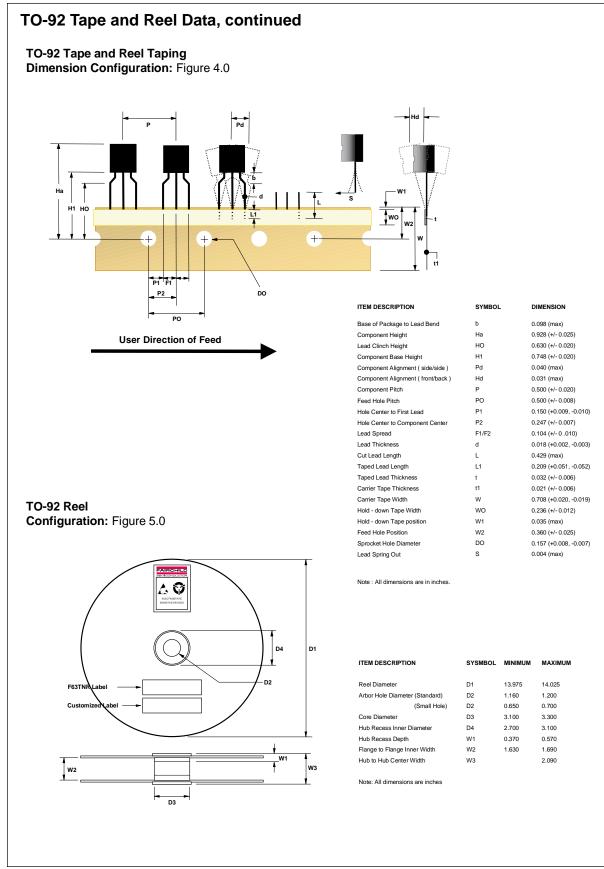


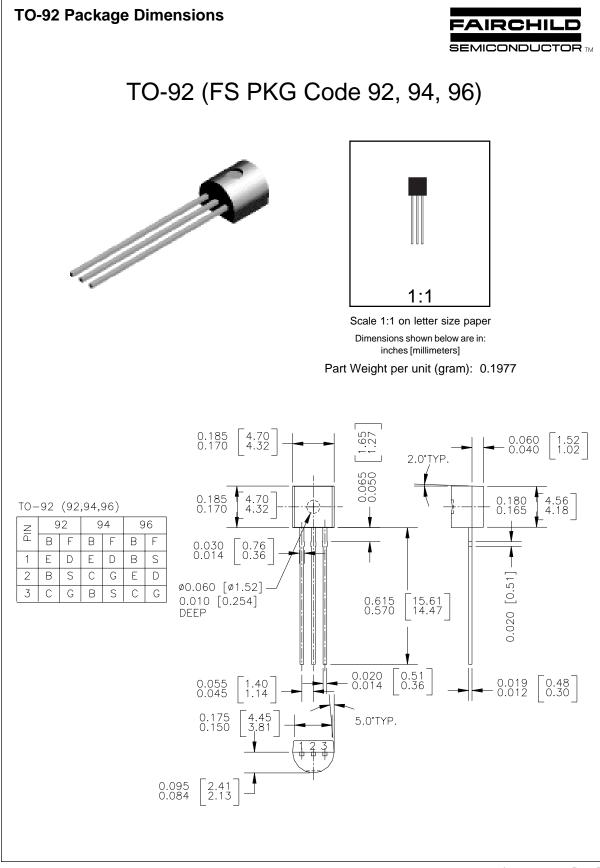
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